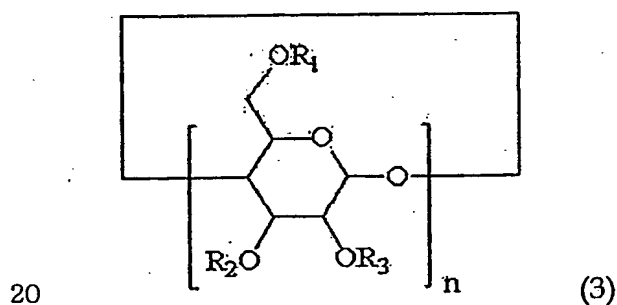


Amendments to the Claims:

Please rewrite the claims as follows:

1. (Original) In an ultra-low dielectric film for a copper interconnect prepared using an organic or inorganic matrix and a cyclodextrin-based template for pore formation, the improvement comprises: said ultra-low dielectric film is prepared by coating with an organic-inorganic mixed solution containing in an organic solvent 40-70 vol% of a polyalkyl silsesquioxane precursor or its copolymer as the matrix and 30-60 vol% of acetylcyclodextrin nanoparticles as the template.
2. (Original) The ultra-low dielectric film for a copper interconnect according to claim 1, wherein said polyalkyl silsesquioxane copolymer is a copolymer of alkyltrialkoxysilane and α ,(-bistrialkoxysilyl)alkane.
3. (Original) The ultra-low dielectric film for a copper interconnect according to claim 2, wherein said polyalkyl silsesquioxane copolymer is a copolymer of methyltrimethoxysilane and (,-bistrimethoxysilyl)ethane or a copolymer of methyltrimethoxysilane and (,-bistriethoxysilyl)ethane.
4. (Original) The ultra-low dielectric film for a copper interconnect according to claim 1, wherein said acetylcyclodextrin is represented by the following formula 3:



wherein n is an integer of 6-8; R1, R2 and R3 are independently a hydrogen atom or an acetyl group; and at least one of R1, R2 and R3 is an acetyl group.

5. (Original) The ultra-low dielectric film for a copper interconnect according to claim 4, wherein said acetylcyclodextrin is selected from the group consisting of triacetyl- α -cyclodextrin, triacetyl- β -cyclodextrin, triacetyl- γ -cyclodextrin, diacetyl- α -cyclodextrin, diacetyl- β -cyclodextrin, diacetyl- γ -cyclodextrin, monoacetyl- α -cyclodextrin, monoacetyl- β -cyclodextrin and monoacetyl- γ -cyclodextrin.

6. (Original) The ultra-low dielectric film for a copper interconnect according to claim 1, wherein said organic solvent is selected from the group consisting of dimethylformamide (DMF), dimethylacrylamide (DMA) and dimethylsulfoxide (DMSO).

7. (Currently Amended) The ultra-low dielectric film for a copper interconnect according to ~~any one of claims 1-6~~ claim 1, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.

8. (New) The ultra-low dielectric film for a copper interconnect according to claim 2, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.

9. (New) The ultra-low dielectric film for a copper interconnect according to claim 3, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.

10. (New) The ultra-low dielectric film for a copper interconnect according to claim 4, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.

11. (New) The ultra-low dielectric film for a copper interconnect according to claim 5, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.

12. (New) The ultra-low dielectric film for a copper interconnect according to claim 6, wherein said ultra-low dielectric film has a maximum porosity of 60% and a minimum dielectric constant of 1.5.